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**Practice for dosimetry in an electron
beam facility for radiation processing at
energies between 300 keV and 25 MeV**

*Pratique de la dosimétrie dans une installation de traitement par
irradiation utilisant un faisceau d'électrons d'énergies comprises
entre 300 keV et 25 MeV*



Reference number
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ISO copyright office
Case postale 56 • CH-1211 Geneva 20
Tel. +41 22 749 01 11
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E-mail copyright@iso.org
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ASTM International, 100 Barr Harbor Drive, PO Box C700,
West Conshohocken, PA 19428-2959, USA
Tel. +610 832 9634
Fax +610 832 9635
E-mail khooper@astm.org
Web www.astm.org

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Foreword

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ASTM International is one of the world's largest voluntary standards development organizations with global participation from affected stakeholders. ASTM technical committees follow rigorous due process balloting procedures.

A project between ISO and ASTM International has been formed to develop and maintain a group of ISO/ASTM radiation processing dosimetry standards. Under this project, ASTM Subcommittee E10.01, Dosimetry for Radiation Processing, is responsible for the development and maintenance of these dosimetry standards with unrestricted participation and input from appropriate ISO member bodies.

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